

Thermoelectric Properties of Ni-doped CoSb₃ Prepared by Encapsulated Induction Melting and Hot Pressing

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Abstract

Ni-doped CoSb₃ was prepared by the encapsulated induction melting and hot pressing, and its doping effects on the thermoelectric properties were investigated. Single phase δ -CoSb₃ was successfully obtained by the subsequent heat treatment at 773K for 24 hours. Nickel atoms acted as electron donors by substituting cobalt atoms. Thermoelectric properties were remarkably improved by the appropriate doping.

Keywords : thermoelectric, skutterudite, doping, induction melting, hot pressing

1. Introduction

The PGEC (phonon-glass and electron-crystal) concept has been considered to search novel thermoelectric materials [1]. Good thermoelectric materials should possess thermal properties similar to that of a glass and electrical properties similar to that of a perfect single crystal material. Skutterudites can satisfy the PGEC concept and CoSb₃ belongs to the skutterudite structure. It is expected to be the most promising thermoelectric material, which can be semiconducting phases by doping and optimizing carrier concentration. It was found that CoSb₃ is a semiconductor and its bandgap is estimated to ~0.5eV. The substitution of Co or Sb by dopants can influence the electronic structure and electrical properties, in particular substantial change of the carrier masses. Furthermore, it can be expected that doping can affect the lattice thermal conductivity due to enhanced phonon scattering on impurities [2]. Although several researchers reported the thermoelectric properties of n-type CoSb₃ doped with different impurities [3,4], the impurity dependence of the transport and thermoelectric properties is still an important subject to be examined. In this study, the encapsulated induction melting and hot pressing were attempted to prepare the Ni-doped CoSb₃ compounds and their doping effects on the thermoelectric properties were investigated.

2. Experimental and Results

Ni-doped CoSb₃ compounds (Co_{1-x}Ni_xSb₃: x=0, 0.005, 0.01, 0.03, 0.05, 0.07, 0.1 and 0.2) were prepared by the encapsulated induction melting, which is widely used to synthesize homogeneous materials. Elemental Co, Ni and

Sb were mixed and melted in an encapsulated quartz ampoule with an RF electrical power of 7kW/40kHz. The EIMed ingots consisted of mixed phases of β -CoSb, γ -CoSb₂, and elemental Sb as well as δ -CoSb₃, but the phases were fully transformed to single δ -CoSb₃ by the subsequent heat treatment at 773K for 24 hours in vacuum. The ingot was crushed into powders and sieved to -325 mesh in a glove box in Ar atmosphere. The powders were hot pressed in a cylindrical Inconel superalloy die at 773K using a stress of 60 MPa for 2 hours in Ar atmosphere. Phase transformations were analyzed for hot-pressed specimens by the high resolution X-ray diffractometer and the field emission scanning electron microscope with the energy dispersive spectrometer. The Ni doping effect on the thermoelectric properties and their temperature dependence were investigated at 300K-700K.

Figure 1 shows the phase analysis by XRD for the hot-pressed Co_{1-x}Ni_xSb₃. Only δ -CoSb₃ was identified for the specimens of x=0 to 0.1, but as shown in Figure 1(c), it decomposed to NiSb₂ and Sb when the x is 0.2, which means the solubility limit of Ni to Co is lower than 0.2.

Figure 2 shows the microstructure of hot-pressed Co_{1-x}Ni_xSb₃. Very sound and compact microstructure with little pores and cracks could be obtained by the hot pressing. Homogeneous specimens were achieved for the x is up to 0.1, but the secondary phases (NiSb₂ and Sb) were observed for Co_{0.8}Ni_{0.2}Sb₃ specimen. This is in good agreement with the XRD analysis results.

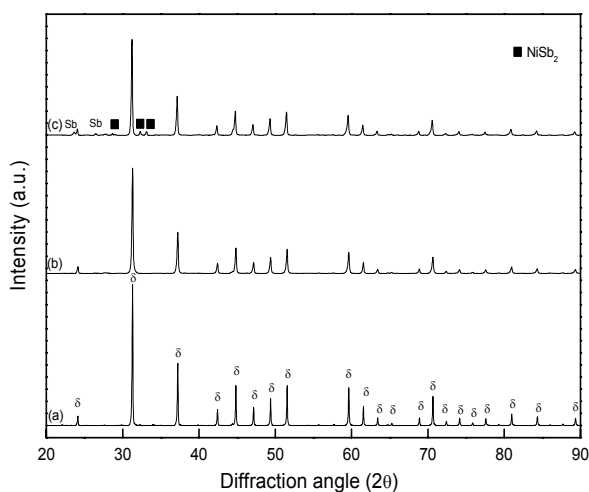


Fig. 1. Phase identifications for hot-pressed $\text{Co}_{1-x}\text{Fe}_x\text{Sb}_3$; (a) $x=0$, (b) $x=0.1$ and (c) $x=0.2$.

Undoped CoSb_3 shows positive Seebeck coefficient, which means the p-type conductivity because its hole effective mass is much smaller than electron effective mass. However, Ni-doped CoSb_3 showed the n-type conductivity at all temperatures examined. Therefore, Ni atoms acted as electron donors by substituting Co atoms as expected. Electrical resistivity of undoped CoSb_3 considerably decreased with increasing temperature, but that of Ni-doped CoSb_3 was almost independent of temperature. Thermal conductivity of undoped CoSb_3 was 0.11 W/cmK at room temperature, and it decreased to 0.07 W/cmK at 700K. Thermal conductivity was drastically reduced by doping. Dopants contribute to electronic thermal conduction as well as phonon scattering centers, which decreases lattice thermal conductivity. However, thermal conductivity of the specimen of $x=0.2$ was higher than that of $x=0.1$. The reason for this was considered as increase in electronic contribution to thermal conductivity due to excess doping.

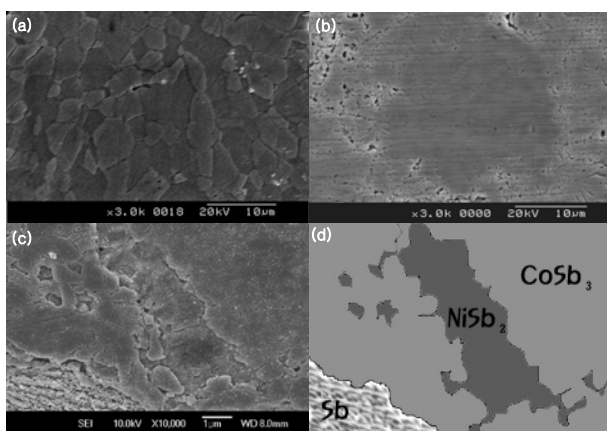


Fig. 2. Microstructures of hot-pressed $\text{Co}_{1-x}\text{Ni}_x\text{Sb}_3$; (a) $x=0$, (b) $x=0.1$, (c) $x=0.2$ and (d) schematic view of the (c).

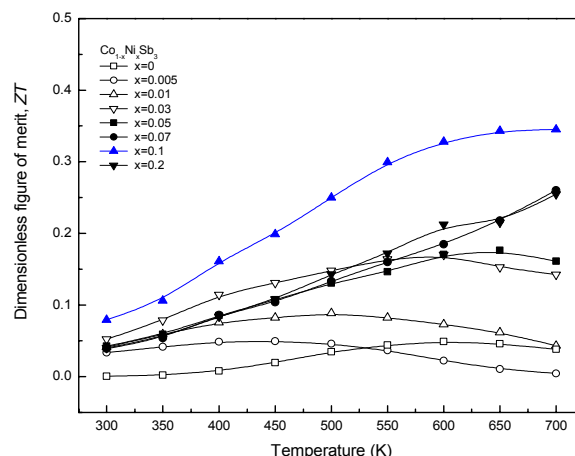


Fig. 3. Dimensionless figure of merit (ZT) of hot-pressed $\text{Co}_{1-x}\text{Ni}_x\text{Sb}_3$.

Figure 3 shows the temperature dependence of dimensionless thermoelectric figure of merit (ZT). Remarkable ZT improvement was obtained by the Ni doping up to $x=0.1$, but it was reduced by excess doping due to decreases in Seebeck coefficient and electrical resistivity and increase in thermal conductivity.

3. Summary

The encapsulated induction melting and hot pressing were employed to prepare Ni-doped CoSb_3 skutterudites and their thermoelectric properties were investigated. Single phase $\delta\text{-CoSb}_3$ was successfully obtained by the subsequent heat treatment at 773K for 24 hours in vacuum. However, $\delta\text{-CoSb}_3$ was decomposed to NiSb_2 and Sb when $x>0.1$, which means that the solubility limit of Ni to Co is $x=0.1$. ZT was considerably enhanced by the Ni doping, and optimum composition was found as $\text{Co}_{0.9}\text{Ni}_{0.1}\text{Sb}_3$ for the Ni-doped CoSb_3 prepared by hot pressing. This was closely related with solubility limit of Ni to Co.

4. Acknowledgments

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5. References

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